

# Preparation and transport properties of $\text{Bi}_{2-x}\text{Cr}_x\text{Se}_3$

Pavĺína Ruleová, Anna Kostelníková, and Āestmír Drařar

*University of Pardubice, Faculty of Chemical Technology, Studentská 573,  
Pardubice 532 10, Czech Republic*

The objective of this work is the synthesis of single crystals  $\text{Bi}_2\text{Se}_3$  with the greatest concentrations of chromium and determine its influence on the transport properties of  $\text{Bi}_2\text{Se}_3$ . The use of chromium, according to our ideas should lead to a reduction in the concentration of free electrons due to the different value of electronegativity Cr and Bi, and thus positively influence the thermoelectric (TE) properties of  $\text{Bi}_2\text{Se}_3$ . In addition to practical application in TE applications,  $\text{Bi}_2\text{Se}_3$  is also examined with respect to magnetic or topological properties [1]. Another issue is the possible development of ferromagnetism or change in topological properties due to the presence of chromium substitution.

Own work describes both the preparation and characterization of single crystal  $\text{Bi}_2\text{Se}_3$  doped with chromium [2]. Single crystals of the composition  $\text{Bi}_{2-x}\text{Cr}_x\text{Se}_3$  where  $x = 0; 0.02; 0.03; 0.04$  were grown from elements of high purity. The purity of the prepared samples was confirmed by X-ray diffraction, which was also used to measure the lattice parameters. Transport properties comprising the Seebeck coefficient  $S$ , Hall coefficient  $R_H$  and the electrical conductivity  $\sigma$  were measured in the temperature range 80-470 K. The transport measurements suggest that the incorporation of chromium atoms in the crystal structure  $\text{Bi}_2\text{Se}_3$  actually leads to a decrease in concentration of free charge carriers apparently due to increased activation energy of formation of native point defects in the crystal. From the data was calculated the value of the power factor  $\sigma S^2$  and the estimated value of the figure of merit  $ZT$  at 370K.

[1] Hor Y.S., Williams A.J., Checkelsky J.G., Roushan P., Seo J., Xu Q., Zandbergen H.W., Yazdani A., Ong N.P., Cava R.J.: Phys. Rev. Lett. 104, 057001-4 (2010).

[2] 2. Kostelníková A., Ruleová P., Drařar Ā: SVOĀ-FChT Pardubice 77-84 (2014).